

# MAPL-000817-015CPC



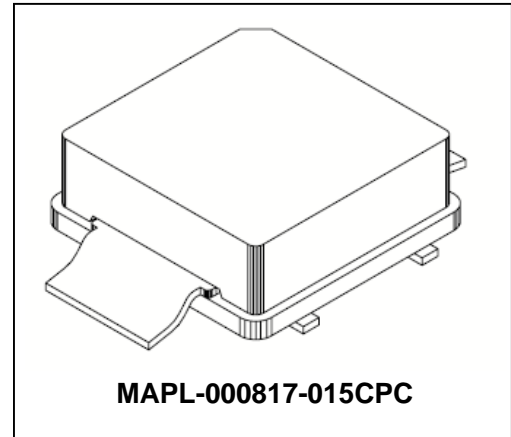
LDMOS RF Line Power FET Transistor  
15 W , 800-1700 MHz, 26V

M/A-COM Products  
Released - Rev. 07.08

## Product Image

Designed for broadband commercial applications up to 1.7GHz

- High gain, high efficiency and high linearity
- Aluminum-Copper Metallization for high reliability
- RoHS Compliant
- Typical P1dB performance at 960MHz, 26Vdc, CW  
Typical power output: 16.5W  
Gain: 17.0dB  
Efficiency: 50%  
10:1 VSWR ruggedness at 15W, 26Vdc, 960MHz



## MAXIMUM RATINGS

Parameter	Symbol	Rating	Units
Drain—Source Voltage	$V_{DS}$	65	$V_{dc}$
Gate—Source Voltage	$V_{GS}$	+20, -20	$V_{dc}$
Total Power Dissipation @ $T_C = 25\text{ }^\circ\text{C}$	$P_D$	31	W
Storage Temperature	$T_{STG}$	-65 to +150	$^\circ\text{C}$
Junction Temperature	$T_J$	200	$^\circ\text{C}$

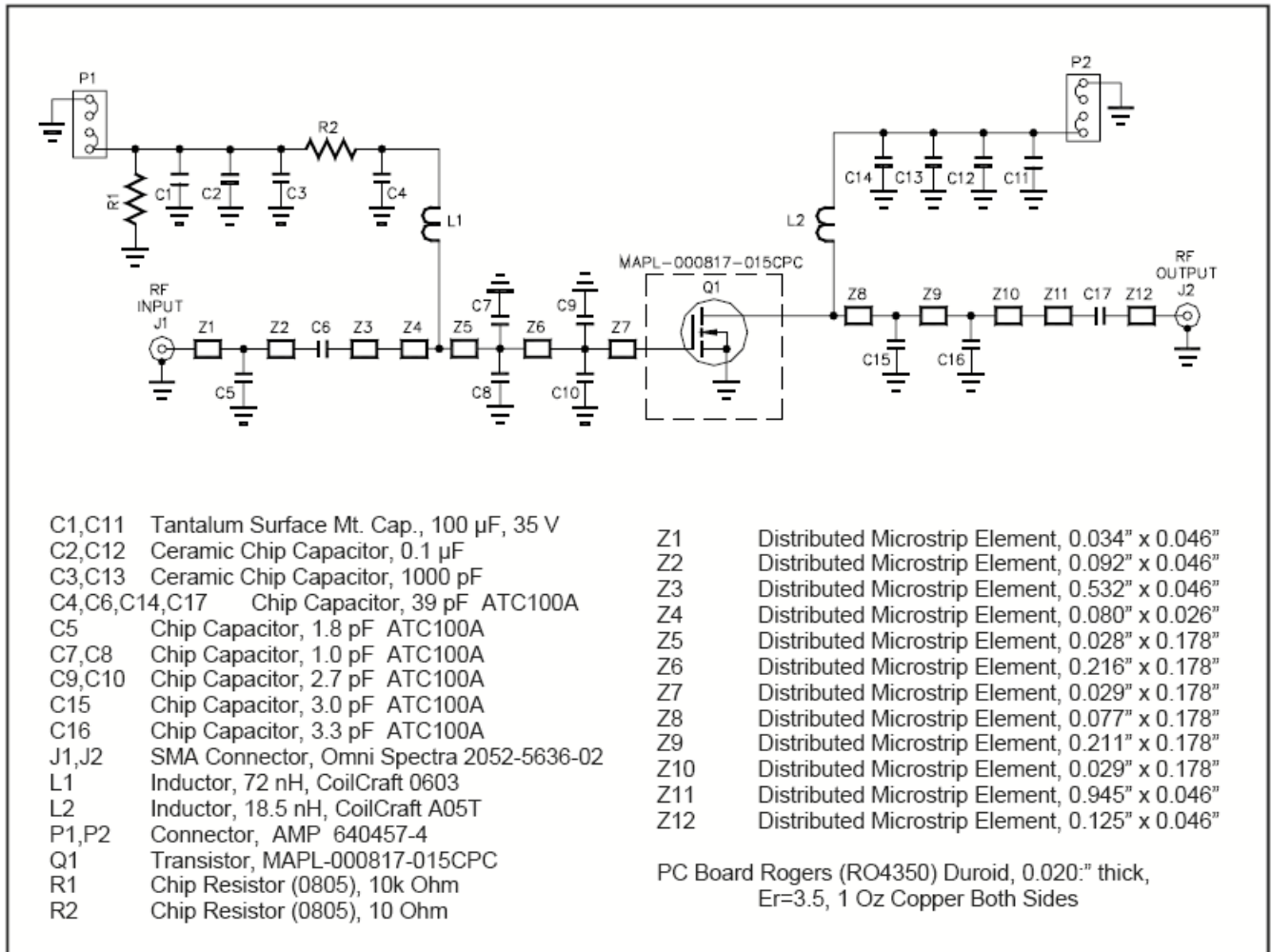
## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	4	$^\circ\text{C/W}$

NOTE—**CAUTION**—MOS devices are susceptible to damage from electrostatic charge. Precautions in handling and packaging MOS devices should be observed.

Characteristic	Symbol	Min	Typ	Max	Unit
<b>DC CHARACTERISTICS @ 25°C</b>					
Drain-Source Breakdown Voltage ( $V_{GS} = 0$ Vdc, $I_D = 20$ $\mu$ Adc)	$V_{(BR)DSS}$	65	—	—	Vdc
Gate Quiescent Voltage ( $V_{ds} = 26$ Vdc, $I_d = 100$ mA)	$V_{DS(Q)}$	3	—	5	Vdc
Drain-Source On-Voltage ( $V_{gs} = 10$ Vdc, $I_d = 1$ A)	$V_{DS(on)}$	—	0.25	—	Vdc
<b>RF FUNCTIONAL TESTS @ 25°C (In M/A-COM Test Fixture) (1)</b>					
Common Source Amplifier Gain ( $V_{DD} = 26$ Vdc, $I_{DQ} = 150$ mA, $f = 960$ MHz, $P_{OUT} = 15$ W)	$G_p$	—	17	—	dB
Drain Efficiency ( $V_{DD} = 26$ Vdc, $I_{DQ} = 150$ mA, $f = 960$ MHz, $P_{OUT} = 15$ W)	EFF ( $\eta$ )	—	50	—	%
Input Return Loss ( $V_{DD} = 26$ Vdc, $I_{DQ} = 150$ mA, $f = 960$ MHz, $P_{OUT} = 15$ W)	IRL	—	-10	—	dB
Output VSWR Tolerance ( $V_{DD} = 26$ Vdc, $I_{DQ} = 150$ mA, $f = 960$ MHz, $P_{OUT} = 15$ W, VSWR = 10:1, All Phase Angles at Frequency of Tests)	$\Psi$	No Degradation In Output Power Before and After Test			
Common Source Amplifier Gain ( $V_{DD} = 26$ Vdc, $I_{DQ} = 150$ mA, $f = 1670$ MHz, $P_{OUT} = 15$ W)	$G_p$	13.0	15	—	dB
Drain Efficiency ( $V_{DD} = 26$ Vdc, $I_{DQ} = 150$ mA, $f = 1670$ MHz, $P_{OUT} = 15$ W)	EFF ( $\eta$ )	45	50	—	%
Input Return Loss ( $V_{DD} = 26$ Vdc, $I_{DQ} = 150$ mA, $f = 1670$ MHz, $P_{OUT} = 15$ W)	IRL	—	-10	-8	dB

(1) Device specifications obtained on a Production Test Fixture.



**Figure 1. 1620-1670 MHz Test Fixture Schematic**

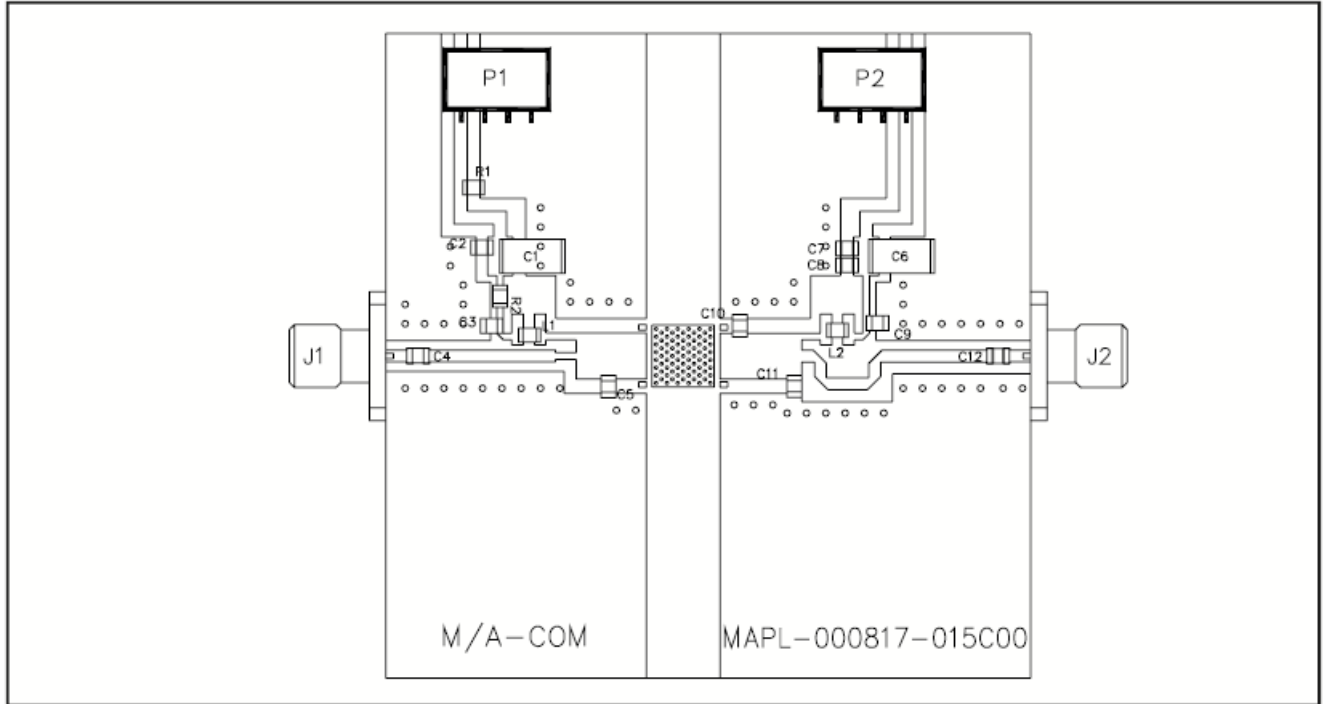
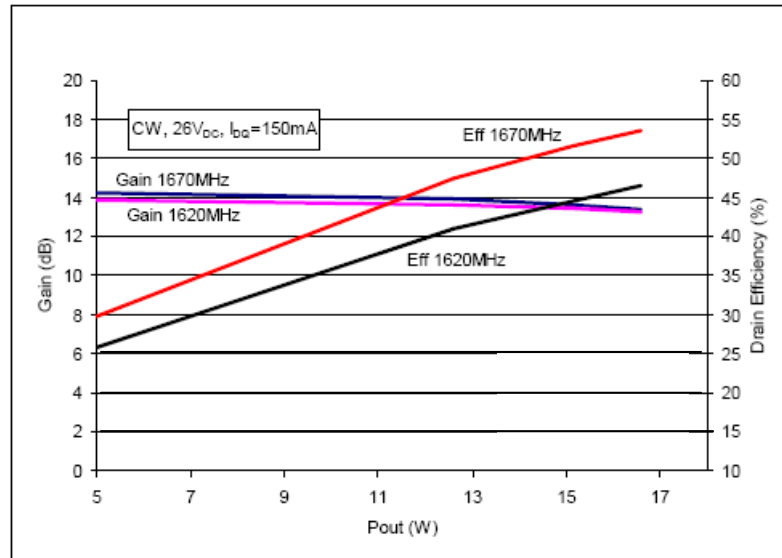
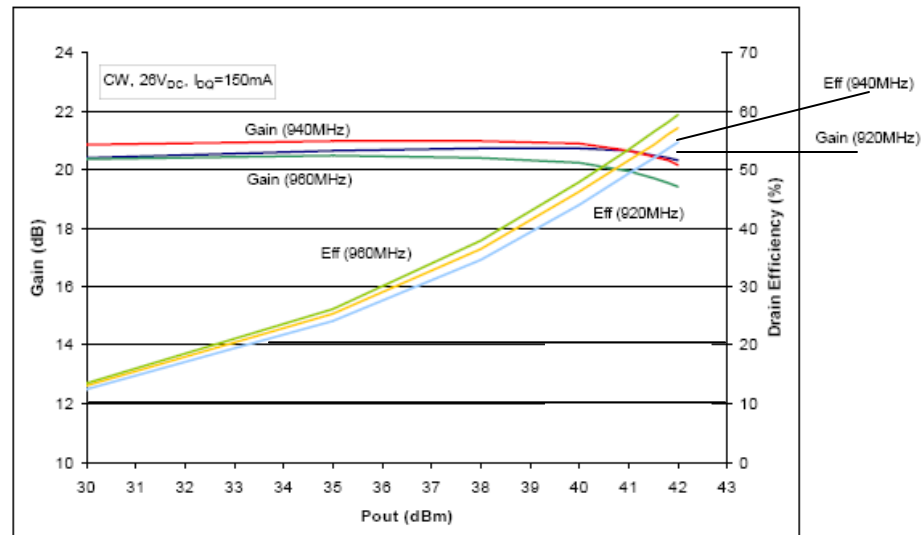


Figure 2. 1620—1670 MHz Test Fixture Component Layout



Graph 1. 1620, 1670MHz: CW Power Gain and Drain Efficiency vs. Output Power



Graph 2. 920, 940, 960MHz: CW Power Gain and Drain Efficiency vs. Output Power

## PACKAGE DIMENSIONS

